

## ABSTRACT OF THE DISCLOSURE

A semiconductor laser device includes a dielectric multilayer film with a reflectance of 40% or more, formed on at least one of optical exit faces of a laser chip, wherein the dielectric multilayer film includes a dielectric film of tantalum oxide ( $\text{Ta}_2\text{O}_5$ ) and another dielectric film of dielectric oxide, such as aluminum oxide ( $\text{Al}_2\text{O}_3$ ), silicon oxide ( $\text{SiO}_2$ ), the tantalum oxide film having an optical absorption coefficient smaller than that of silicon (Si) film and thermal stability in emission superior to that of titanium oxide ( $\text{TiO}_2$ ) film, thereby remarkably improving the COD degradation level.